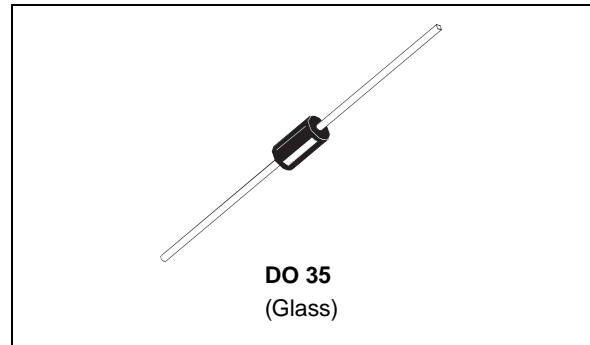


SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

Metal to silicon junction diode featuring high breakdown, low turn-on voltage and ultrafast switching. Primarily intended for high level UHF/VHF detection and pulse application with broad dynamic range.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	60	V
I_F	Forward Continuous Current*	$T_a = 25^\circ\text{C}$ 15	mA
I_{FSM}	Surge non Repetitive Forward Current*	$t_p \leq 1\text{s}$ 50	mA
T_{stg} T_j	Storage and Junction Temperature Range	- 65 to 200 - 65 to 200	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering during 10s at 4mm from Case	230	$^\circ\text{C}$

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
$R_{th(j-a)}$	Junction-ambient*	400	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions	Min.	Typ.	Max.	Unit
V_{BR}	$T_{amb} = 25^\circ\text{C}$ $I_R = 10\mu\text{A}$	60			V
V_F^{**}	$T_{amb} = 25^\circ\text{C}$ $I_F = 1\text{mA}$			0.41	V
	$T_{amb} = 25^\circ\text{C}$ $I_F = 15\text{mA}$			1	
I_R^{**}	$T_{amb} = 25^\circ\text{C}$ $V_R = 50\text{V}$			0.2	μA

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions	Min.	Typ.	Max.	Unit
C	$T_{amb} = 25^\circ\text{C}$ $V_R = 0\text{V}$ $f = 1\text{MHz}$			2.2	pF
τ	$T_{amb} = 25^\circ\text{C}$ $I_F = 5\text{mA}$ Krakauer Method			100	ps

* On infinite heatsink with 4mm lead length

** Pulse test: $t_p \leq 300\mu\text{s}$ $\delta < 2\%$.

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

Fig.1 : Forward current versus forward voltage (typical values).

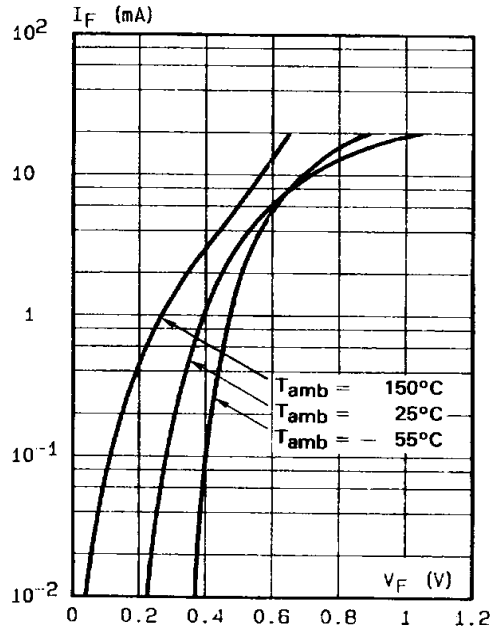


Fig.2 : Capacitance C versus reverse applied voltage V_R (typical values).

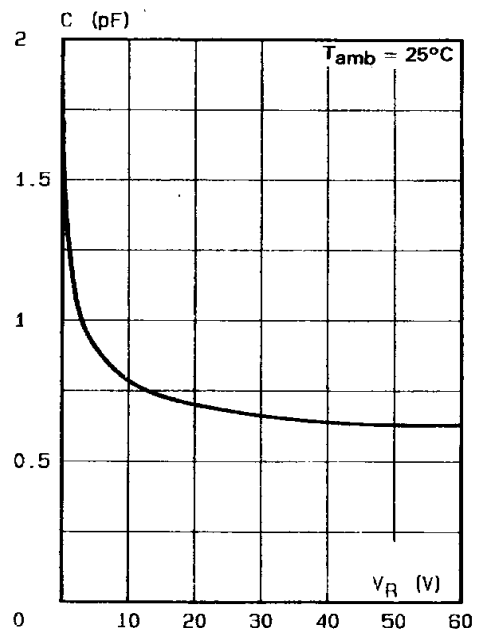


Fig.3 : Reverse current versus ambient temperature.

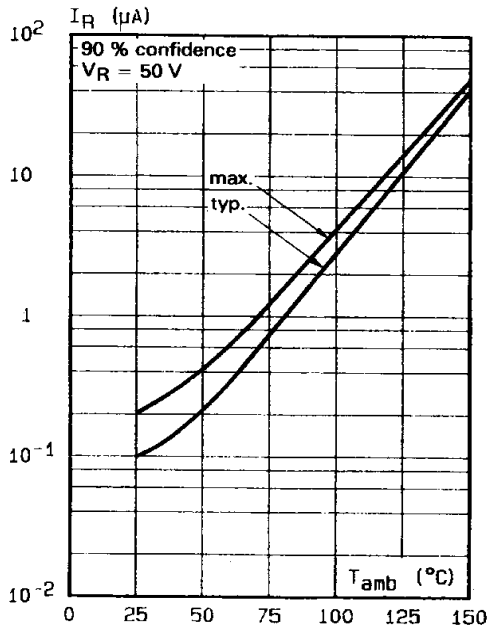
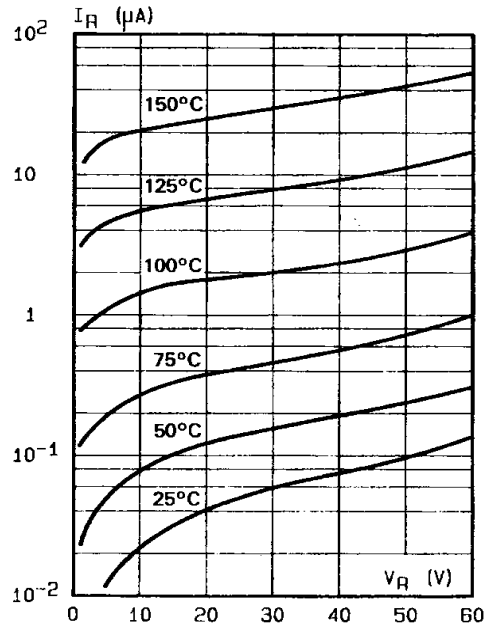
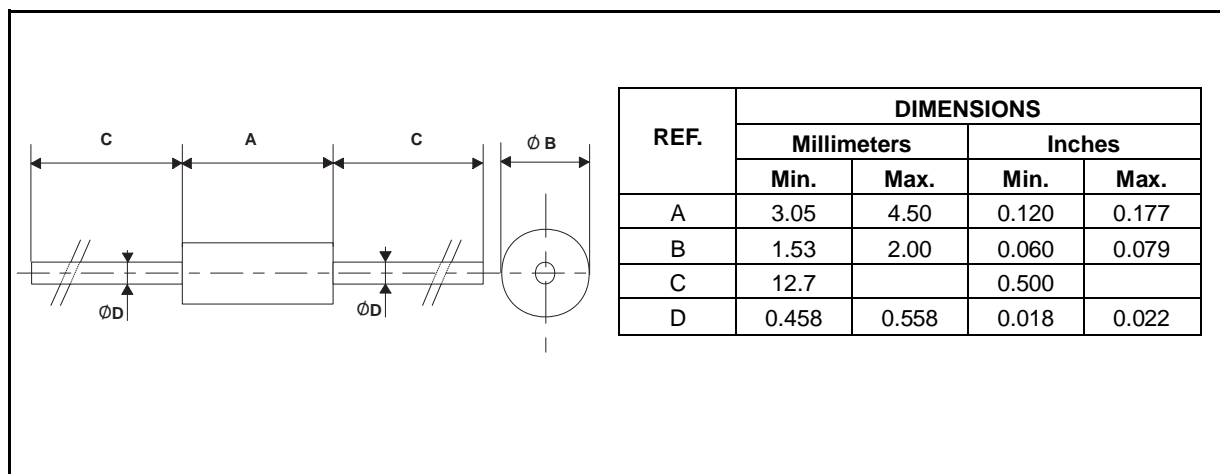


Fig.4 : Reverse current versus continuous reverse voltage (typical values).



PACKAGE MECHANICAL DATA

DO 35 Glass



Cooling method : by convection and conduction

Marking: clear, ring at cathode end.

Weight: 0.15g

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